

2SD1991A

Silicon NPN epitaxial planar type

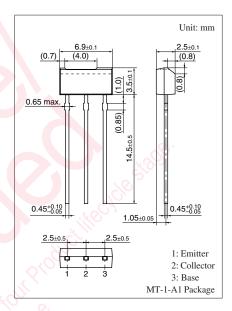
For general amplification Complementary to 2SB1320A

■ Features

- High forward current transfer ratio h_{FE}
- ullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- Allowing supply with the radial taping

■ Absolute Maximum Ratings $T_a = 25$ °C

Symbol	Rating	Unit
V_{CBO}	60	V
V_{CEO}	50	V
V _{EBO}	7	V
I_{C}	100	mA
I_{CP}	200	mA
P _C	400	mW
T _j	150	°C
T _{stg}	-55 to +150	°C
	$\begin{array}{c} V_{CBO} \\ V_{CEO} \\ V_{EBO} \\ I_{C} \\ I_{CP} \\ P_{C} \\ T_{j} \end{array}$	V _{CBO} 60 V _{CEO} 50 V _{EBO} 7 I _C 100 I _{CP} 200 P _C 400 T _j 150



■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	$I_C = 10 \mu\text{A}, I_E = 0$	60	20)		V
Collector-emitter voltage (Base open)	V _{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	50	0		V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu A, I_C = 0$	7			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 20 \text{ V}, I_{E} = 0$			1	μΑ
Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}, I_{B} = 0$			1	μΑ
Forward current transfer ratio	h _{FE1} *	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	160		460	_
	h _{FE2}	$V_{CE} = 2 \text{ V}, I_{C} = 100 \text{ mA}$	90			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$		0.1	0.3	V
Transition frequency	f_T	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		150		MHz
Collector output capacitance	C _{ob}	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		3.5		pF
(Common base, input open circuited)						

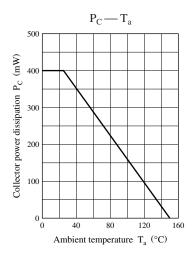
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

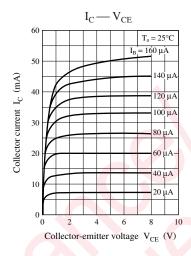
2. *: Rank classification

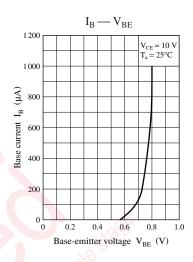
Rank	Q	R	S	No rank
h_{FE1}	160 to 260	210 to 340	290 to 460	160 to 460

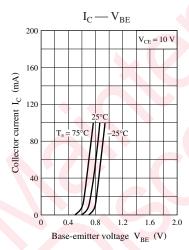
Product of no-rank classification is not marked.

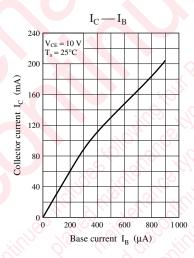
Publication date: April 2003 SJC00234BED 1

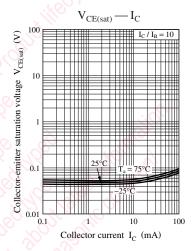


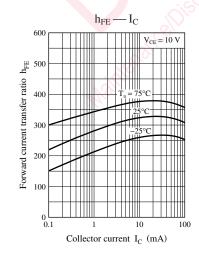


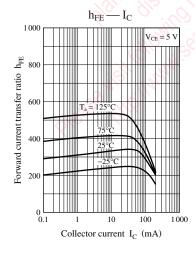


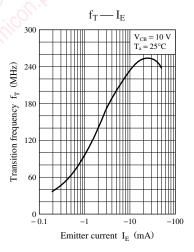






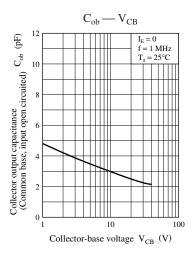


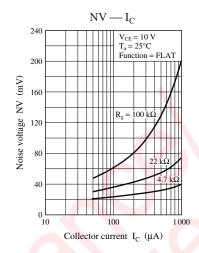


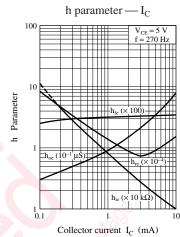


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